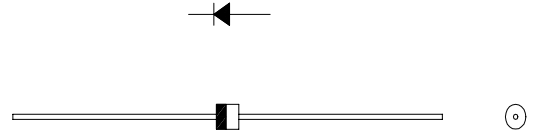


DIODE Type : 11ES1

OUTLINE DRAWING

FEATURES

- * Miniature Size
- * Low Forward Voltage drop
- * Low Reverse Leakage Current
- * High Surge Capability
- * 26mm and 52mm Inside Tape Spacing Package Available



Maximum Ratings

Approx Net Weight:0.17g

Rating	Symbol	11ES1			Unit
Repetitive Peak Reverse Voltage	V_{RRM}	100			V
Non-repetitive Peak Reverse Voltage	V_{RSM}	250			V
Average Rectified Output Current	I_O	0.98	$T_a=25^{\circ}C$ *1	50Hz Half Sine Wave Resistive Load	A
		1.0	$T_a=50^{\circ}C$ *2		
RMS Forward Current	$I_{F(RMS)}$	1.57			A
Surge Forward Current	I_{FSM}	45	50Hz Half Sine Wave, 1cycle, Non-repetitive		A
Operating Junction Temperature Range	T_{jw}	- 40 to + 150			$^{\circ}C$
Storage Temperature Range	T_{stg}	- 40 to + 150			$^{\circ}C$

Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit	
Peak Reverse Current	I_{RM}	$T_j= 25^{\circ}C, V_{RM}= V_{RRM}$	-	-	50	μA	
Peak Forward Voltage	V_{FM}	$T_j= 25^{\circ}C, I_{FM}= 1.0A$	-	-	1.0	V	
Thermal Resistance	$R_{th(j-a)}$	Junction to Ambient	*1	-	-	140	$^{\circ}C/W$
			*2			110	

*1:Without Fin or P.C. Board

*2:P.C. Board Mounted (L=3mm,Print Land=5x5mm,Both Sides)

11ES1 OUTLINE DRAWING (Dimensions in mm)

